## Noninverting Buffer / CMOS Logic Level Shifter with LSTTL-Compatible Inputs

The MC74VHCT50A is a hex noninverting buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffered output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0 V CMOS logic to 5.0 V CMOS Logic or from 1.8 V CMOS logic to 3.0 V CMOS Logic while operating at the high-voltage power supply.

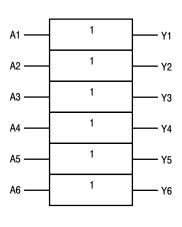
The MC74VHCT50A input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHCT50A to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when  $V_{\rm CC}$  = 0 V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

#### **Features**

- High Speed:  $t_{PD} = 3.5 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 2 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2.0 \text{ V}$
- $\bullet$  CMOS–Compatible Outputs:  $V_{OH}$  > 0.8  $V_{CC};\,V_{OL}$  < 0.1  $V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

# A1 1 2 Y1 A2 3 4 Y2 A3 5 6 Y3 Y = A A4 9 8 Y4 A5 11 10 Y5 A6 13 12 Y6

#### LOGIC SYMBOL





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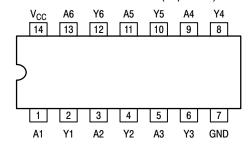
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14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G

### PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

#### **FUNCTION TABLE**

A Input	Y Output
L	L
Н	Н

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol		Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		$-0.5 \le V_{  } \le +7.0$	V
V <sub>OUT</sub>	DC Output Voltage	Output in HIGH or LOW State	$-0.5 \le V_{O} \le +7.0$	V
I <sub>IK</sub>	DC Input Diode Current		-20	mA
I <sub>OK</sub>	DC Output Diode Current		±20	mA
Io	DC Output Source/Sink Current		±25	mA
I <sub>CC</sub>	DC Supply Current per Supply Pir	1	±50	mA
I <sub>GND</sub>	DC Ground Current per Ground P	in	±50	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Ca	se for 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
θЈΑ	Thermal Resistance	(Note 1) SOIC TSSOP	125 170	°C/W
P <sub>D</sub>	Power Dissipation in Still Air	SOIC TSSOP	500 450	mW
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 200 2000	V
I <sub>Latch-Up</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 5)	±300	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

#### RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V <sub>CC</sub>	2.0	5.5	V
DC Input Voltage	V <sub>IN</sub>	0.0	5.5	V
DC Output Voltage $V_{CC} = 0$ High or Low State	V <sub>OUT</sub>	0.0 0.0	5.5 V <sub>CC</sub>	V
Operating Temperature Range	T <sub>A</sub>	-55	+125	°C
Input Rise and Fall Time $ V_{CC} = 3.3 \ V \pm 0.3 \ V \\ V_{CC} = 5.0 \ V \pm 0.5 \ V $	t <sub>r</sub> , t <sub>f</sub>	0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

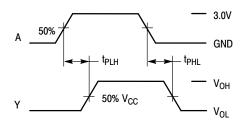
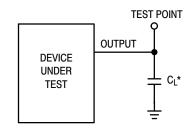


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	٦	Γ <sub>A</sub> = 25°(	<b>C</b>	T <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ 1	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	٧
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OH} = -4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \end{split}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	٧
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	V <sub>IN</sub> = V <sub>CC</sub> or GND	5.5			2.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65	mA
I <sub>OFF</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μА

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### AC ELECTRICAL CHARACTERISTICS ( $C_{load} = 50 \text{ pF}$ , Input $t_r = t_f = 3.0 \text{ns}$ )

				7	Γ <sub>A</sub> = 25°(	)	T <sub>A</sub> ≤	85°C	<b>T</b> <sub>A</sub> ≤ 1	125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propogation Delay,	$V_{CC} = 3.3 \pm 0.3 \text{ V}$	$C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0			ns
	Input A to Y	$V_{CC} = 5.0 \pm 0.5 \text{ V}$	$C_L = 15 pF$ $C_L = 50 pF$		6.2 7.0	7.5 8.5		8.5 9.5		9.5 10.5	
C <sub>IN</sub>	Maximum Input Capacitance				5	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Note 6)	15	рF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

#### **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> =	T <sub>A</sub> = 25°C	
Symbol	Characteristic	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.8	1.0	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.8	-1.0	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		2.0	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		0.8	V

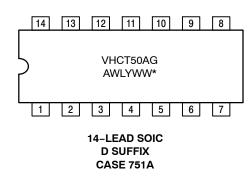
#### **ORDERING INFORMATION**

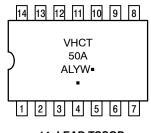
Device	Package	Shipping <sup>†</sup>
MC74VHCT50ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74VHCT50ADTR2G	TSSOP-14	0500 / Tono 9 Dool
NLVVHCT50ADTR2G*	(Pb-Free)	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **MARKING DIAGRAMS**

(Top View)





14-LEAD TSSOP DT SUFFIX CASE 948G

A = Assembly Location

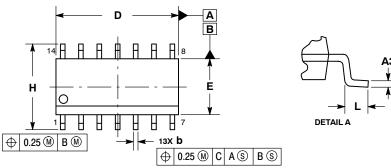
WL, L = Wafer Lot Y = Year WW, W = Work Week G or ■ = Pb-Free Package

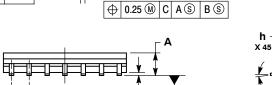
<sup>\*</sup>NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

<sup>\*</sup>See Applications Note #AND8004/D for date code and traceability information.

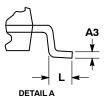
#### **PACKAGE DIMENSIONS**

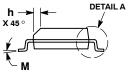
#### SOIC-14 NB **D SUFFIX** CASE 751A-03 ISSUE K





C SEATING PLANE



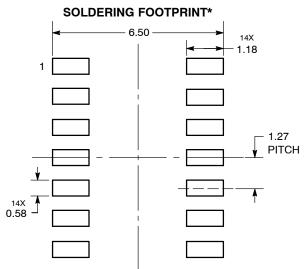


#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
  4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
  5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050	BSC
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

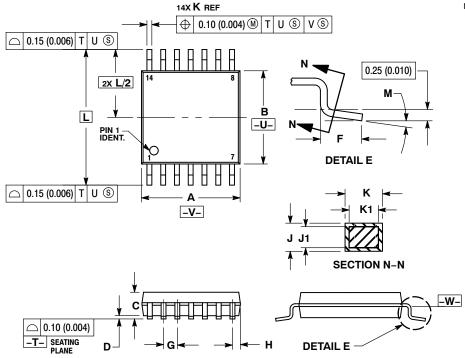


DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

#### TSSOP-14 CASE 948G **ISSUE B**



#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

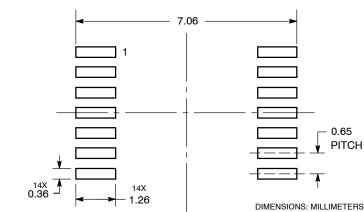
  2. CONTROLLING DIMENSION: MILLIMETER.
- B. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE
- DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE
  DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0 °	8 °	0 °	8 °	

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